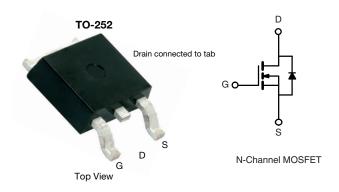


**Vishay Siliconix** 

# Automotive N-Channel 300 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	300			
$R_{DS(on)}\left(\Omega\right)$ at $V_{GS}$ = 10 V	0.330			
I <sub>D</sub> (A)	10			
Configuration	Single			



#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified <sup>d</sup>
- 100 %  $R_a$  tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD10N30-330H-GE3			

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	300	V	
Gate-Source Voltage	V <sub>GS</sub>	± 30	v		
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	10		
	T <sub>C</sub> = 125 °C		5		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	50	А		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	16			
Single Pulse Avalanche Current <sup>e</sup>	L = 0.05 mH	I <sub>AS</sub>	12.65		
Single Pulse Avalanche Energy <sup>e</sup>	L = 0.05 MH	E <sub>AS</sub>	4	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	107	W	
Maximum Fower Dissipation 5	T <sub>C</sub> = 125 °C		35	vv	
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.4	0/10	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

e. 1.5 k $\Omega$  resistance in series with the gate.

S15-1136-Rev. C, 12-May-15

Document Number: 67070



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		300	-	-		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.8	4.4	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 30 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 300 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = 300 V, $T_{J}$ = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS}$ = 300 V, $T_J$ = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	А	
		$V_{GS} = 10 V$	I <sub>D</sub> = 14 A	-	0.275	0.330		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}$	I <sub>D</sub> = 14 A, T <sub>J</sub> = 125 °C	-	-	0.733	Ω	
		$V_{GS} = 10 V$	I <sub>D</sub> = 14 A, T <sub>J</sub> = 175 °C	-	-	1.000		
$\label{eq:Forward} Forward\ Transconductance\ ^{b} \qquad \qquad g_{fs} \qquad \qquad V_{DS} = 15\ V,\ I_{D} = 14\ A$				-	26	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	1749	2190	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	112	140		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	44	55		
Total Gate Charge <sup>c</sup>	Qg			-	31	47		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{GS} = 10 V$	$V_{DS} = 150 \text{ V}, \text{ I}_{D} = 7 \text{ A}$	-	8	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	9.6	-	1	
Gate Resistance	Rg		f = 1 MHz	0.4	0.8	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 150 \text{ V}, \text{ R}_{\text{L}} = 21 \Omega$ $\text{I}_{\text{D}} \cong 7 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	18	28	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	20	30		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	16	А	
Forward Voltage	V <sub>SD</sub>	$I_{\rm F} = 25 \text{ A}, V_{\rm GS} = 0 \text{ V}$		_	0.9	1.5	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

VISHAY www.vishay.com SQD10N30-330H

T<sub>C</sub> = 25 °C

= 125 °C

4

 $T_C = 25 °C$ 

6

Coss

40

60

V<sub>DS</sub> - Drain-to-Source Voltage (V)

Capacitance

80

100

9

I<sub>D</sub> - Drain Current (A)

Transconductance

C<sub>iss</sub>

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- 55 °C Г<sub>С</sub> =

10

8

T<sub>C</sub> = - 55 °C

T<sub>C</sub> = 125 °C

12

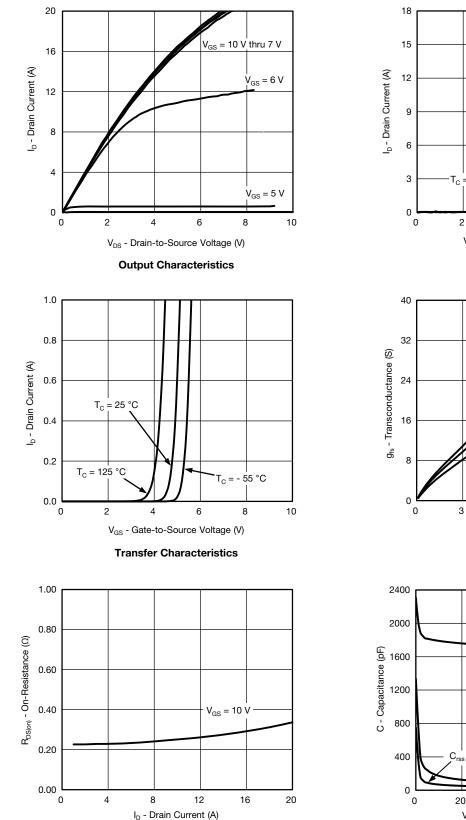
15

6

V<sub>GS</sub> - Gate-to-Source Voltage (V)

**Transfer Characteristics** 

## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



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S15-1136-Rev. C, 12-May-15

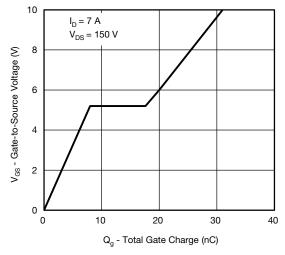
**On-Resistance vs. Drain Current** 

<sup>3</sup> 

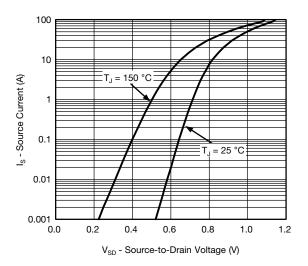


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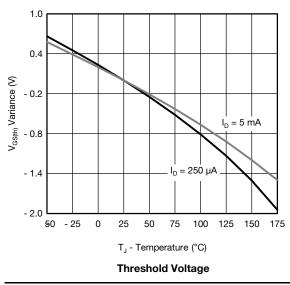
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

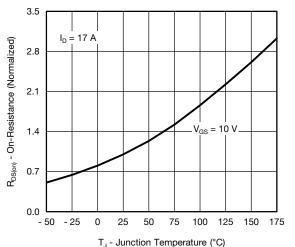


Gate Charge

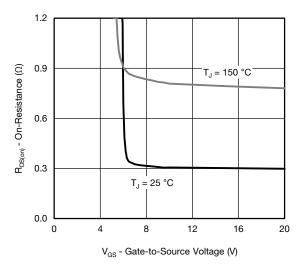


Source Drain Diode Forward Voltage

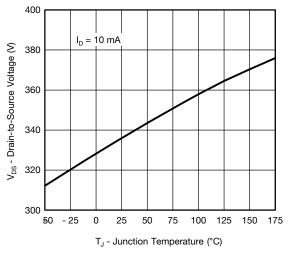




**On-Resistance vs. Junction Temperature** 







Drain Source Breakdown vs. Junction Temperature

S15-1136-Rev. C, 12-May-15

4

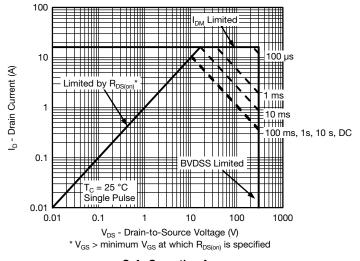
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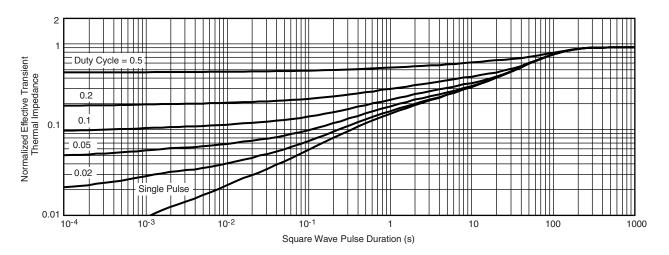


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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Safe Operating Area

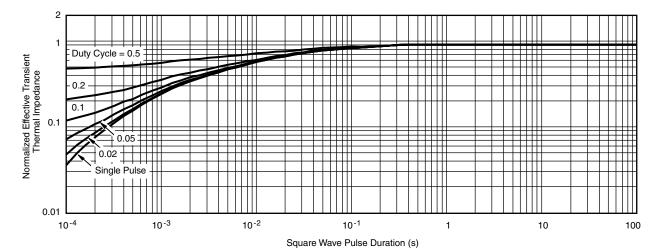


Normalized Thermal Transient Impedance, Junction-to-Ambient



## **Vishay Siliconix**

## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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#### **REVISION HISTORY**<sup>a</sup>

REVISION	DATE	DESCRIPTION OF CHANGE
В	26-Feb-2015	UIS changed
С	04-May-2015	• R <sub>g</sub> , C <sub>iss</sub> and t <sub>r</sub> updated

Note

a. As of April 2014





Е b3 Ľ Δ ŝ b2 e1 Б E1

# C2 т gage plane height (0.5 mm)

-C

- A1

**TO-252AA** Case Outline

	MILLIN	<b>IETERS</b>	INCHES		
DIM.	MIN. MAX.		MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC 0.090 BSC				
e1	4.56	4.56 BSC		BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
	ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

• Dimension L3 is for reference only.





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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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